**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability of 1000 mW

# 3. Applications

- LED driver
- Power management
- Low-side load switch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	4.4	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 3.7 \text{ A}; T_j = 25 \text{ °C}$		-	36	44	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u> </u>	D
2	S	source		
3	D	drain	1 2	G (i) 44)
			TO-236AB (SOT23)	017aaa253

# 6. Ordering information

### Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV40UN2	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

# 7. Marking

#### Table 4. Marking codes

9 •••••					
	Type number	Marking code			
		[1]			
	PMV40UN2	%K8			

[1] % = placeholder for manufacturing site code

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	4.4	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	3.7	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	2.3	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	16	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	490	mW
			[1]	-	1000	mW
		T <sub>sp</sub> = 25 °C		-	5000	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode	1				
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.9	Α

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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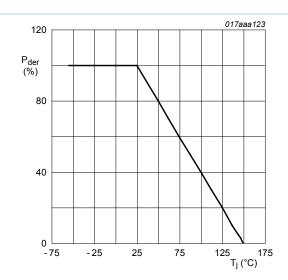


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times \textbf{100 \%}$$

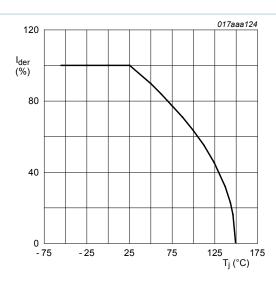


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

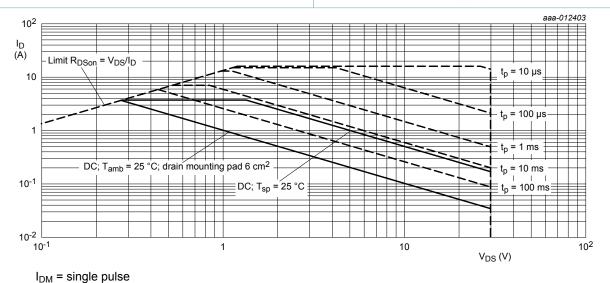


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	R <sub>th(j-a)</sub> thermal resistance from junction to ambient		[1]	-	217	255	K/W
			<u>[2]</u>	-	105	124	K/W
		t ≤ 5 s	[2]	-	73	86	K/W

PMV40UN2

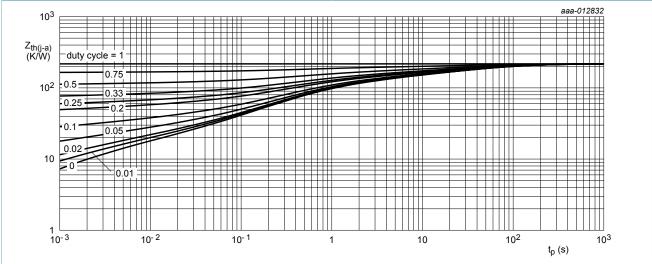
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	20	25	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

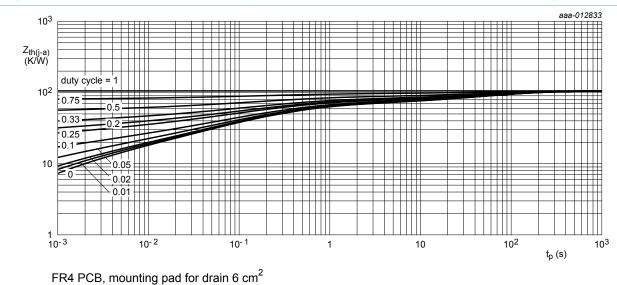


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.7 A; T <sub>j</sub> = 25 °C	-	36	44	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.7 A; T <sub>j</sub> = 150 °C	-	62	75	mΩ
		$V_{GS}$ = 2.5 V; $I_D$ = 3.4 A; $T_j$ = 25 °C	-	43	53	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 0.5 A; T <sub>j</sub> = 25 °C	-	56	78	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 2 A; $T_{j}$ = 25 °C	-	10.9	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	8.7	-	Ω
Dynamic ch	naracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_D$ = 3.7 A; $V_{GS}$ = 4.5 V;	-	7	12	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.9	-	nC
$Q_{GD}$	gate-drain charge		-	1.7	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	635	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	40	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	35	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $I_D$ = 3.7 A; $V_{GS}$ = 4.5 V;	-	9	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	23	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	34	-	ns
t <sub>f</sub>	fall time		-	12	-	ns
Source-dra	in diode		ı	1	-	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 0.9 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.7	1.2	V

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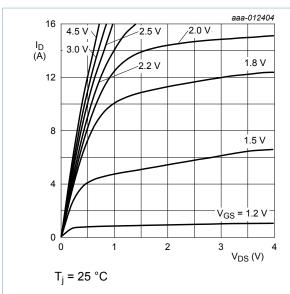


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

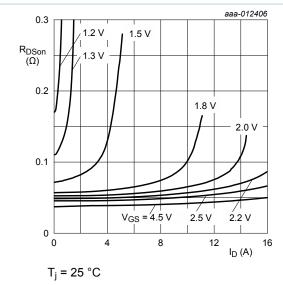


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

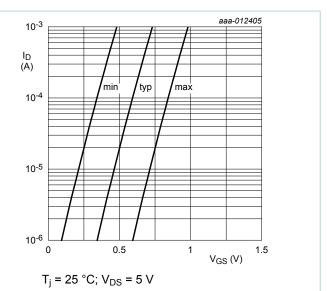


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

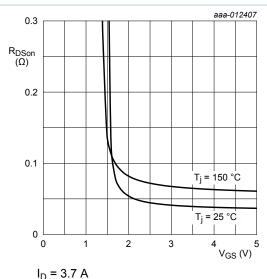
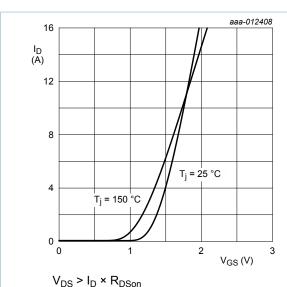


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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VDS / ID ^ KDSon

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

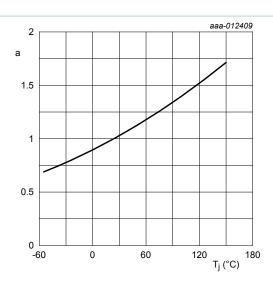


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

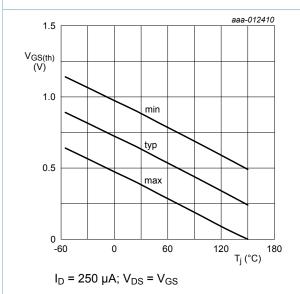


Fig. 12. Gate-source threshold voltage as a function of junction temperature

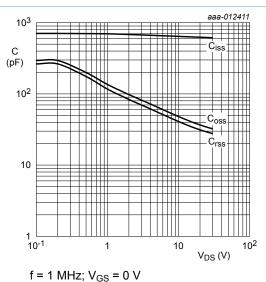


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 30 V, N-channel Trench MOSFET

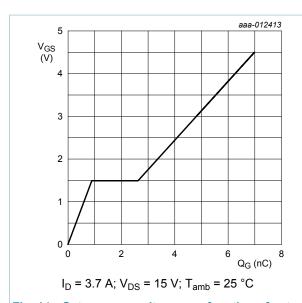


Fig. 14. Gate-source voltage as a function of gate charge; typical values

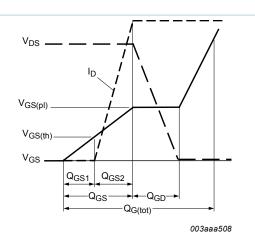


Fig. 15. MOSFET transistor: Gate charge waveform definitions

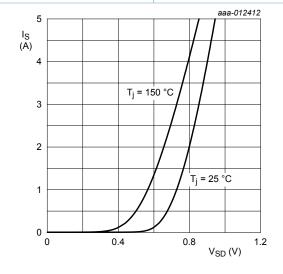
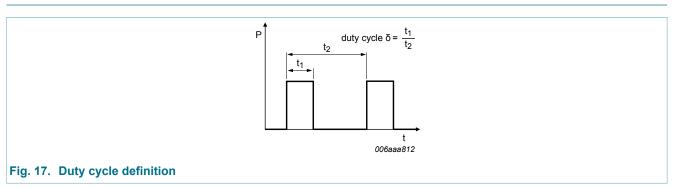


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



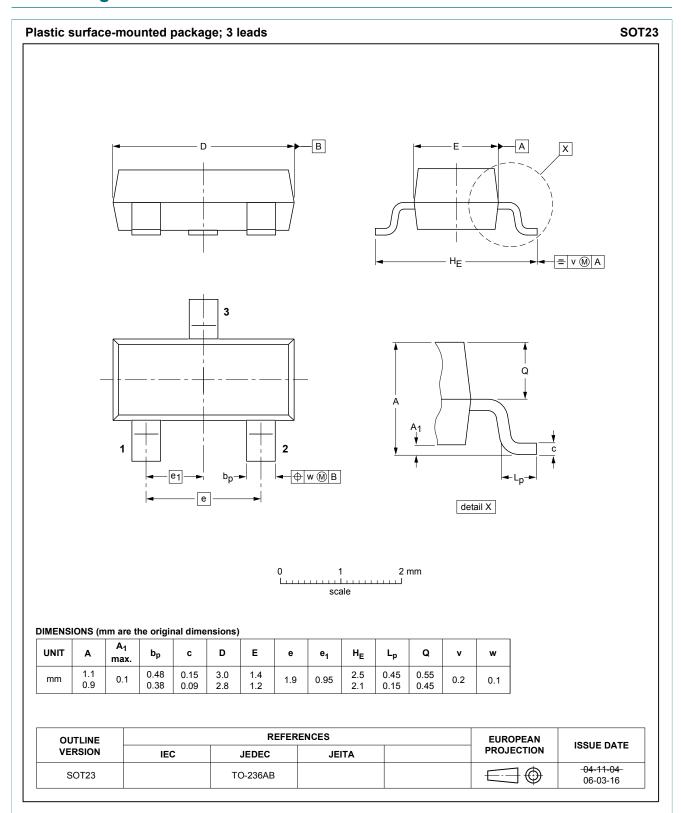
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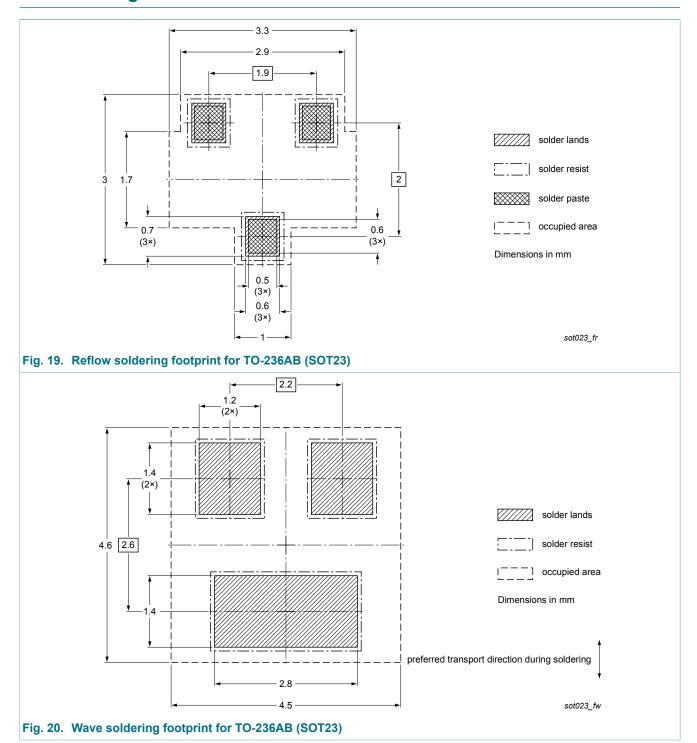
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# 12. Package outline



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## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV40UN2 v.1	20140424	Product data sheet	-	-

#### 30 V, N-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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